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SEMICONDUCTOR DEVICE MANUFACTURING METHOD

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[There are no amendments to this patent.]

Claims

1. Semiconductor device manufacturing method consisting of a process wherein a first metal projection formed on a first substrate and an electrode on a first substrate, on which a semiconductor element is formed, are stacked together, then subjected to pressure and heated, and with the first metal projection on the aforementioned first substrate being transferred and bonded onto the electrode on the second substrate, as well as consisting of a process wherein next the second electrode of a third substrate, having a first electrode for an external connecting lead and the aforementioned second electrode, in a position corresponding to the electrode on the aforementioned second substrate, and on which a semiconductor element is formed, and the electrode on the aforementioned second substrate, having the aforementioned first metal projection, are stacked together, then subjected to pressure and heated, and with the electrodes on the aforementioned second and third substrates being bonded to each other via the aforementioned first metal projection.

2. The semiconductor device manufacturing method described in Claim 1, wherein a first electrode on a third substrate and a second metal projection formed on an external connecting lead are positioned together, then subjected to pressure and heated so as to bond.

3. The semiconductor device manufacturing method described in Claim 1, wherein metal projections are formed via a multilayer

metal film on an electrode for an external connecting lead on a third substrate, and with the film lead, which is an external connecting lead, being bonded to the aforementioned metal projections.

4. The semiconductor device manufacturing method described in Claim 1, wherein the electrode on the second substrate and the second electrode on the third substrate are bonded via the first metal projection, and with the first electrode of the third substrate and wiring on a circuit board being connected by fine metal wires.

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